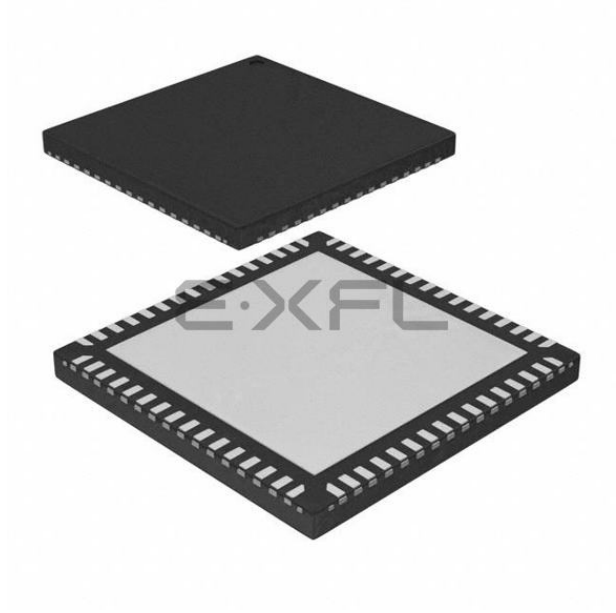
Silicon Labs - EFM32WG230F64-QFN64T Datasheet



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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

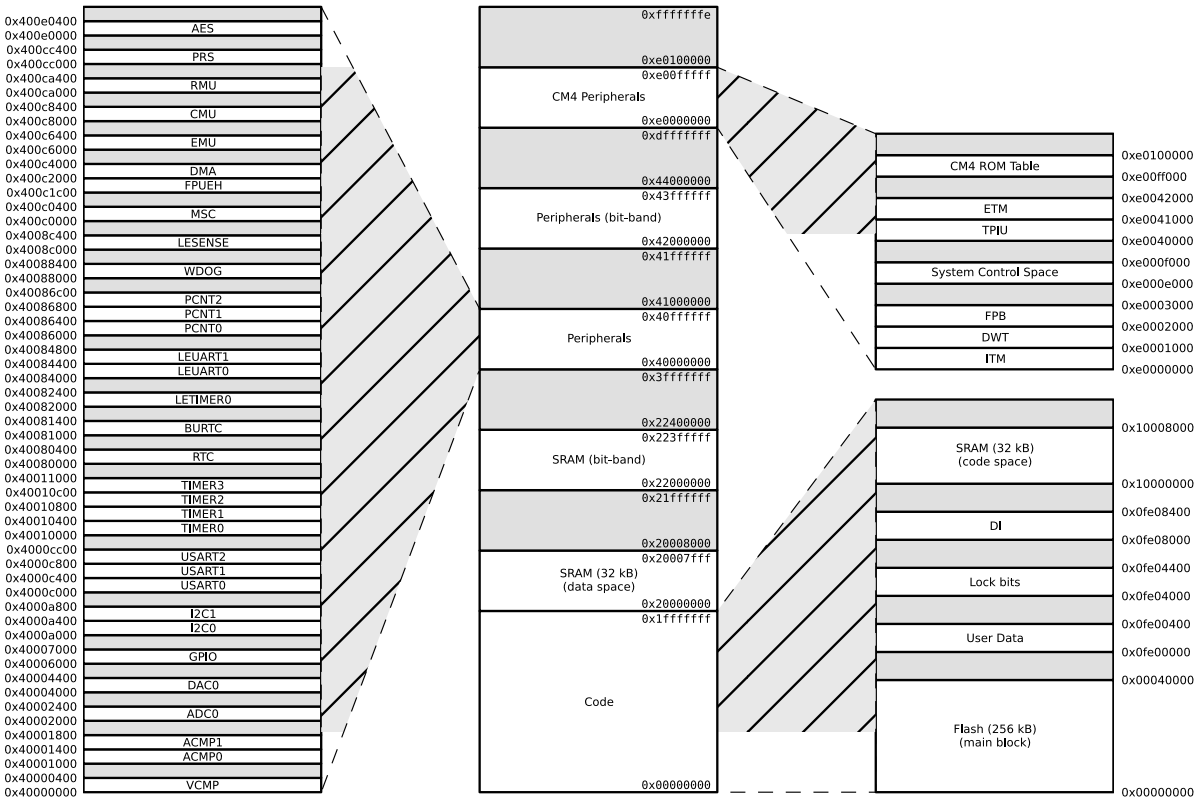
Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	56
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg230f64-qfn64t

Module	Configuration	Pin Connections
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	56 pins	Available pins are shown in Table 4.3 (p. 60)

2.3 Memory Map

The *EFM32WG230* memory map is shown in Figure 2.2 (p. 8), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32WG230 Memory Map with largest RAM and Flash sizes



3.3.2 Environmental

Table 3.3. Environmental

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ESDHBM}	ESD (Human Body Model HBM)	T_{AMB}=25°C			1000	V
V_{ESDCDM}	ESD (Charged Device Model, CDM)	T_{AMB}=25°C			500	V

Latch-up sensitivity passed: ±100 mA/1.5 × V_{SUPPLY}(max) according to JEDEC JESD 78 method Class II, 85°C.

3.4 Current Consumption

Table 3.4. Current Consumption

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{EM0}	EM0 current. No prescaling. Running prime number calculation code from Flash. (Production test condition = 14 MHz)	48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		225	236	µA/MHz
		48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		225		µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		226	238	µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		227		µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		228	240	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		229		µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		230	243	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		231		µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		232	245	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		233		µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		238	250	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		238		µA/MHz

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=85°C		3.0[1]	4.0[1]	µA
I_{EM3}	EM3 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.65	1.3	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		2.65	4.0	µA
I_{EM4}	EM4 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.02	0.055	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		0.44	0.9	µA

[1]Using backup RTC.

3.4.1 EM1 Current Consumption

Figure 3.1. EM1 Current consumption with all peripheral clocks disabled and HFXO running at 48MHz

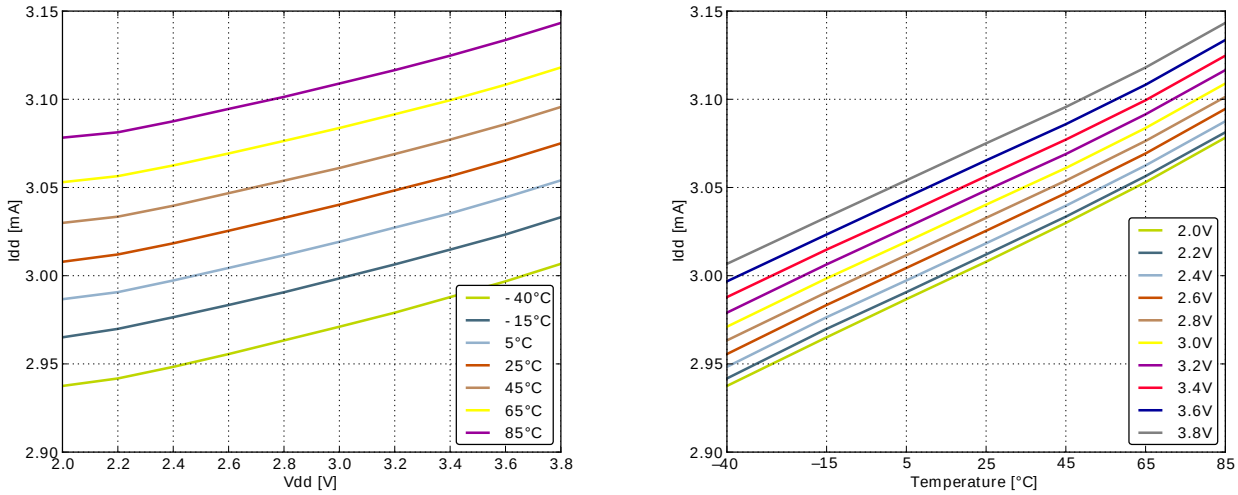
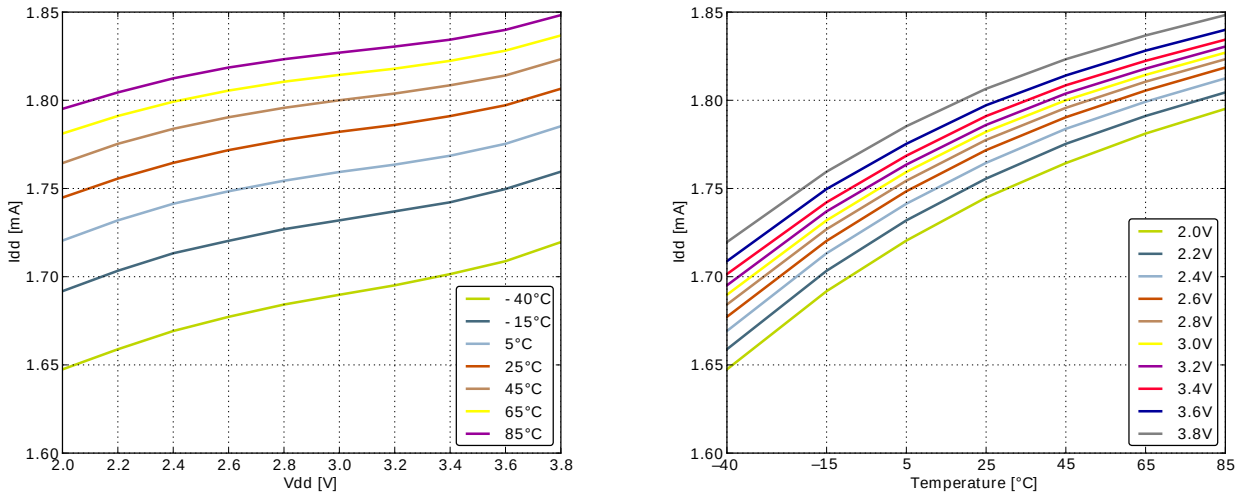
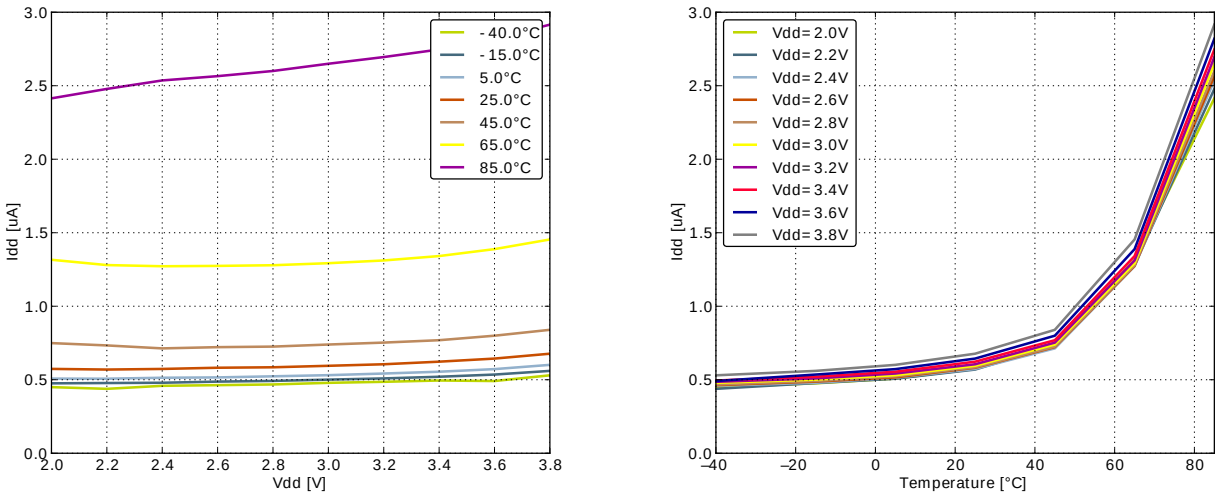


Figure 3.2. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28MHz



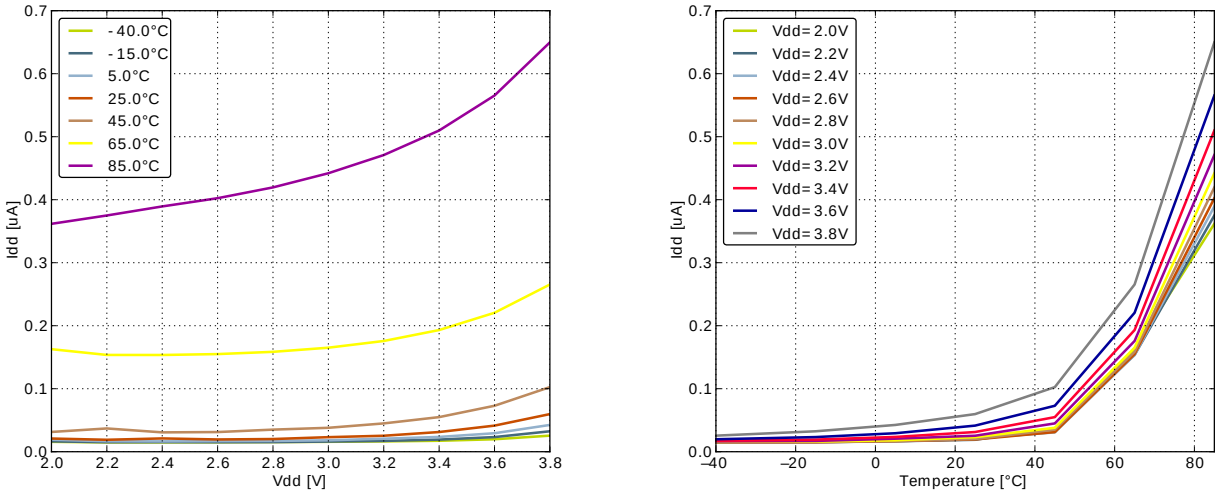
3.4.3 EM3 Current Consumption

Figure 3.9. EM3 current consumption.



3.4.4 EM4 Current Consumption

Figure 3.10. EM4 current consumption.



3.5 Transition between Energy Modes

The transition times are measured from the trigger to the first clock edge in the CPU.

Table 3.5. Energy Modes Transitions

Symbol	Parameter	Min	Typ	Max	Unit
t_{EM10}	Transition time from EM1 to EM0		0		HF-CORE-CLK cycles
t_{EM20}	Transition time from EM2 to EM0		2		µs
t_{EM30}	Transition time from EM3 to EM0		2		µs
t_{EM40}	Transition time from EM4 to EM0		163		µs

3.6 Power Management

The EFM32WG requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

Table 3.6. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage		1.74		1.96	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85	1.98	V
$V_{PORthr+}$	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t_{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF

3.7 Flash

Table 3.7. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{PERASE}	Page erase time		20	20.4	20.8	ms
t_{DERASE}	Device erase time		40	40.8	41.6	ms
I_{ERASE}	Erase current				7[1]	mA
I_{WRITE}	Write current				7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

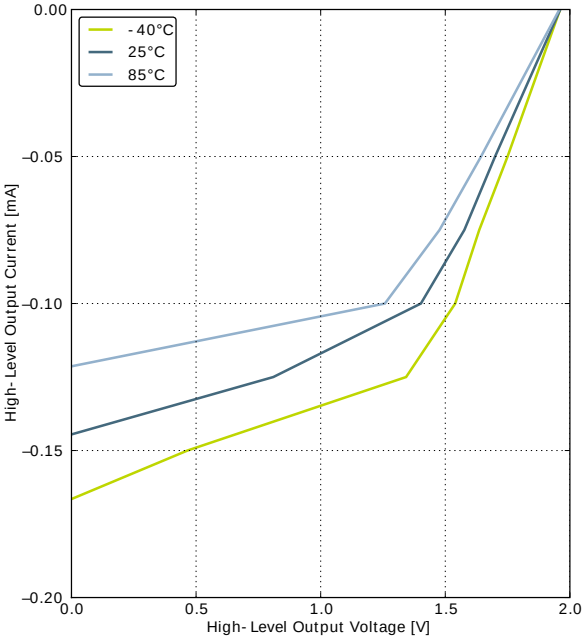
[1]Measured at 25°C

3.8 General Purpose Input Output

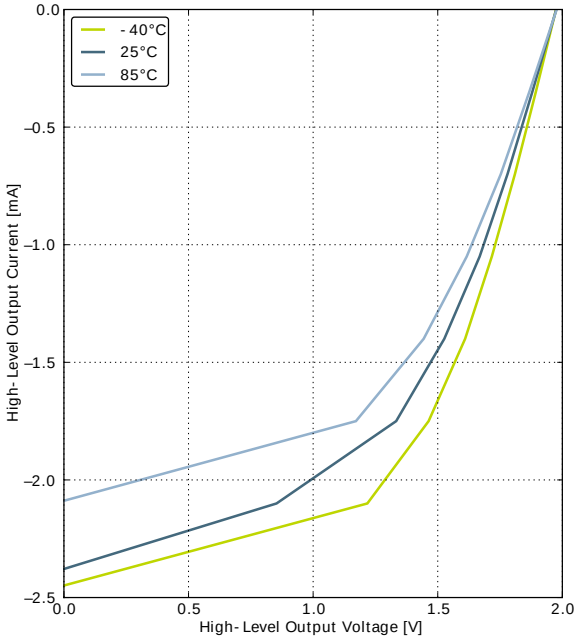
Table 3.8. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				0.30V_{DD}	V
V_{IOIH}	Input high voltage		0.70V_{DD}			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V_{DD}		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V_{DD}		V
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V_{DD}		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V_{DD}		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V_{DD}			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V_{DD}			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V_{DD}			V
		Sourcing 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V_{DD}			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V_{DD}		V
		Sinking 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V_{DD}		V
		Sinking 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V_{DD}		V
		Sinking 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V_{DD}		V
		Sinking 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V_{DD}	V
		Sinking 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V_{DD}	V
		Sinking 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V_{DD}	V

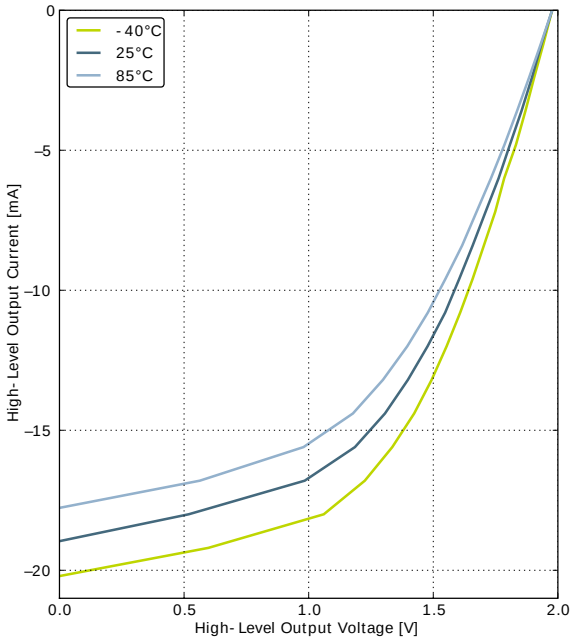
Figure 3.12. Typical High-Level Output Current, 2V Supply Voltage



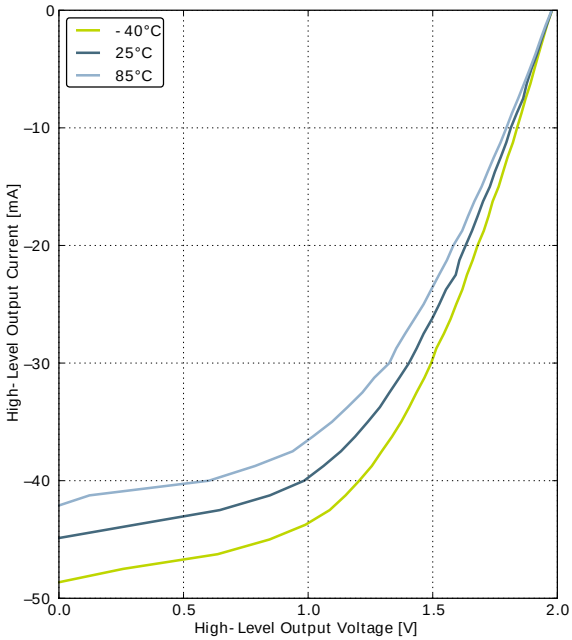
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.9. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		X[1]		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L=10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L=10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

[1]See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the energyAware Designer in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.10. HFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		48	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 48 MHz			50	Ohm
		Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L=20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		µA
		32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		µA
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		µs

Figure 3.22. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature

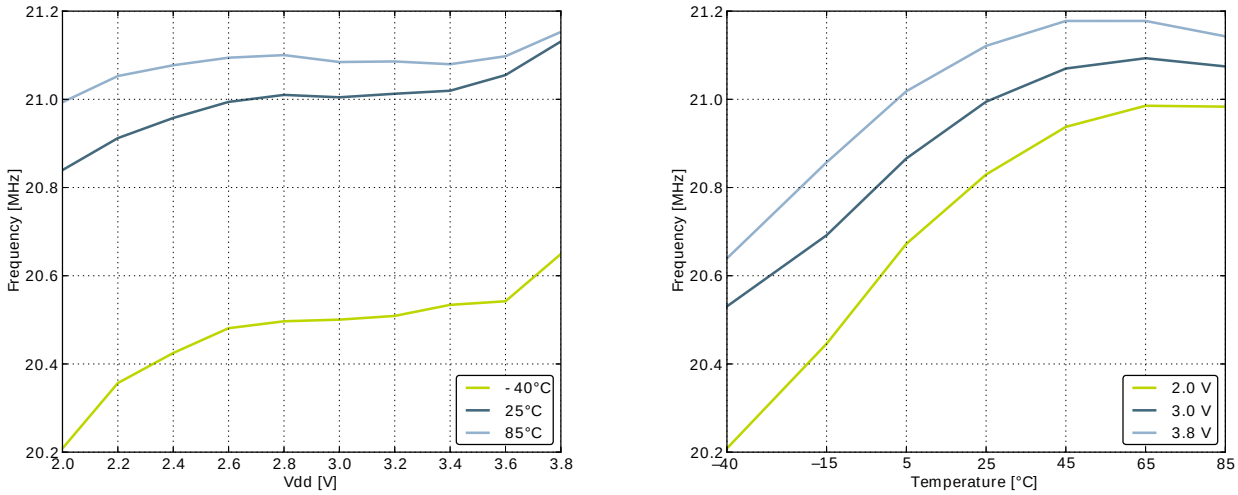
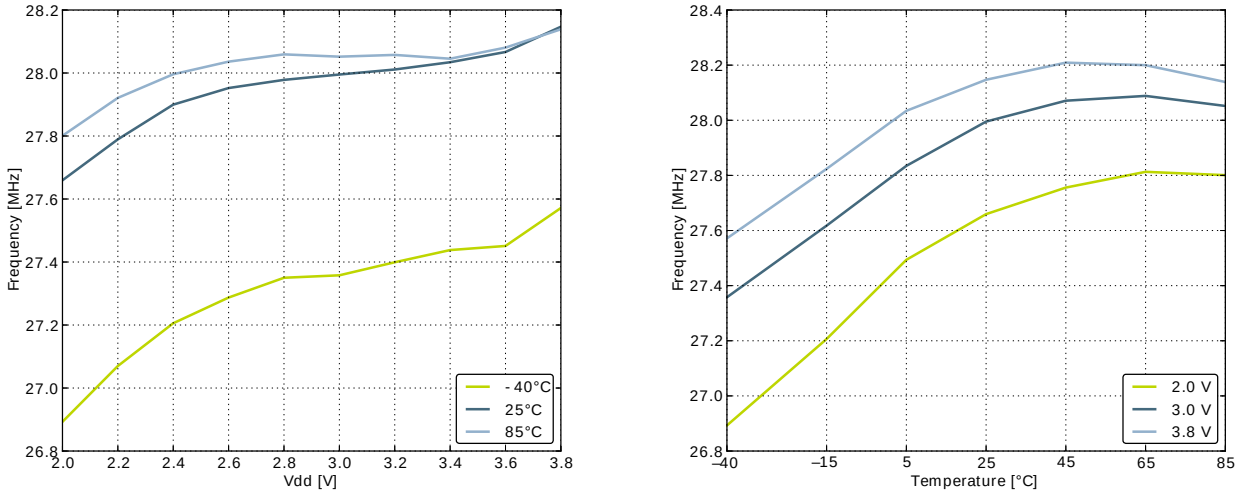


Figure 3.23. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature



3.9.5 AUXHFRCO

Table 3.13. AUXHFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$f_{AUXHFRCO}$	Oscillation frequency, V_{DD}= 3.0 V, T_{AMB}=25°C	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48	6.60	6.72	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
$t_{AUXHFRCO\_settling}$	Settling time after start-up	$f_{AUXHFRCO}$ = 14 MHz		0.6		Cycles
$DC_{AUXHFRCO}$	Duty cycle	$f_{AUXHFRCO}$ = 14 MHz	48.5	50	51	%
$TUNESTEP_{AUXHFRCO}$	Frequency step for LSB change in TUNING value			0.3[1]		%

[1]The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

3.9.6 ULFRCO

Table 3.14. ULFRCO

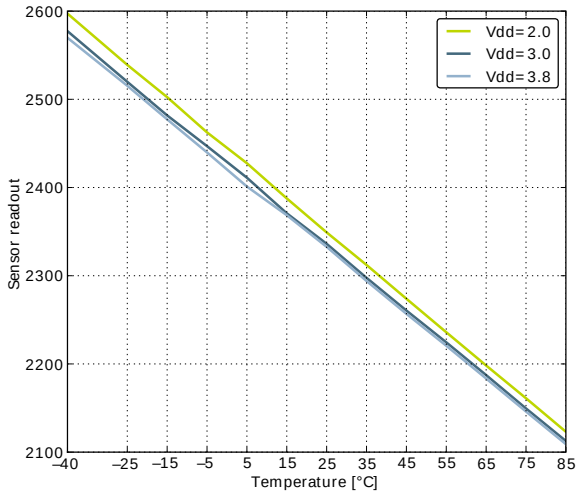
Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{ULFRCO}	Oscillation frequency	25°C, 3V	0.7		1.75	kHz
TC_{ULFRCO}	Temperature coefficient			0.05		%/°C
VC_{ULFRCO}	Supply voltage coefficient			-18.2		%/V

3.10 Analog Digital Converter (ADC)

Table 3.15. ADC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ADCIN}	Input voltage range	Single ended	0		V_{REF}	V
		Differential	$-V_{REF}/2$		$V_{REF}/2$	V
$V_{ADCREFIN}$	Input range of external reference voltage, single ended and differential		1.25		V_{DD}	V
$V_{ADCREFIN\_CH7}$	Input range of external negative reference voltage on channel 7	See $V_{ADCREFIN}$	0		V_{DD} - 1.1	V
$V_{ADCREFIN\_CH6}$	Input range of external positive ref-	See $V_{ADCREFIN}$	0.625		V_{DD}	V

Figure 3.31. ADC Temperature sensor readout



3.11 Digital Analog Converter (DAC)

Table 3.16. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
		VDD voltage reference, differential	$-V_{DD}$		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12 bit		400[1]		µA
		100 kSamples/s, 12 bit		200[1]		µA
		1 kSamples/s 12 bit NORMAL		17[1]		µA
SR_{DAC}	Sample rate				500	ksamples/s
f_{DAC}	DAC clock frequency	Continuous Mode			1000	kHz
		Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
$CYC_{DACCONV}$	Clock cyckles per conversion			2		
$t_{DACCONV}$	Conversion time		2			µs
$t_{DACSETTLE}$	Settling time			5		µs
SNR_{DAC}	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		58		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		196		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		229		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=0		1230		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=1		2130		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		1630		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		2590		μV_{RMS}

Figure 3.32. OPAMP Common Mode Rejection Ratio

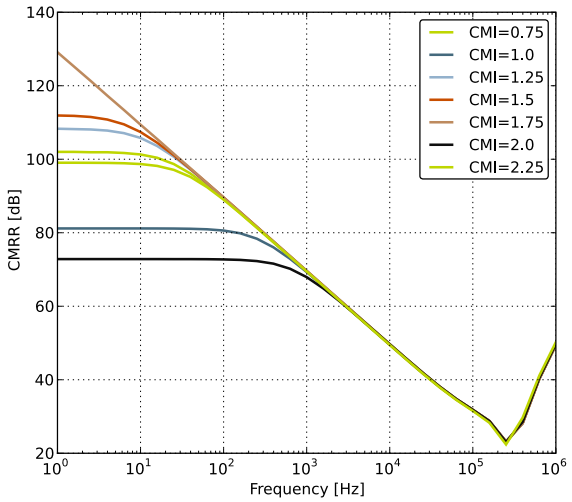
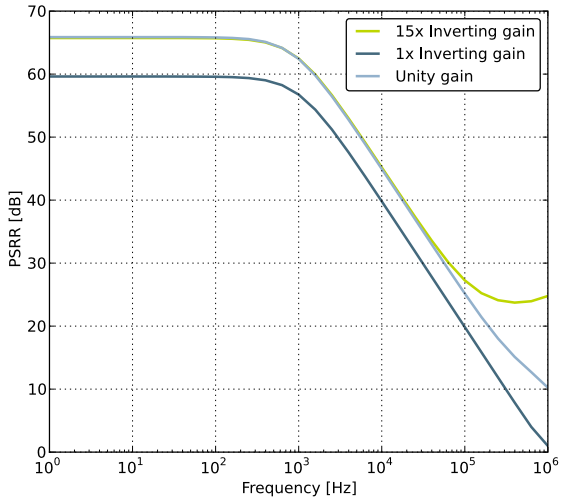


Figure 3.33. OPAMP Positive Power Supply Rejection Ratio



3.13 Analog Comparator (ACMP)

Table 3.18. ACMP

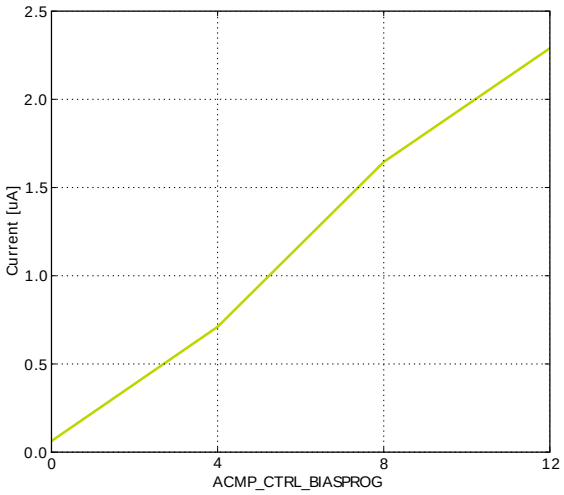
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULLBIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.4	µA
		BIASPROG=0b1111, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	15	µA
		BIASPROG=0b1111, FULLBIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	µA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		µA
		Internal voltage reference		5		µA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm
$t_{ACMPSTART}$	Startup time				10	µs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 46) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

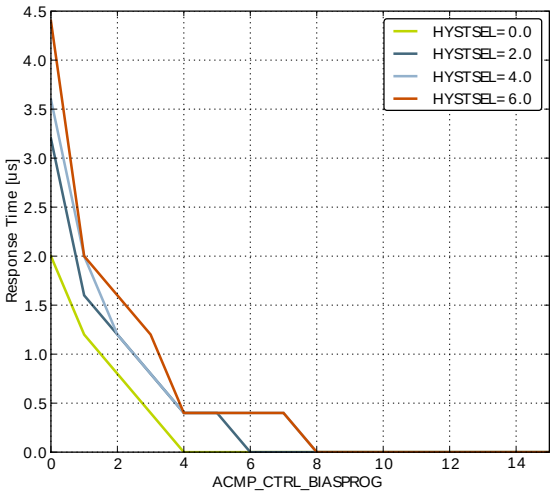
Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \quad (3.1)$$

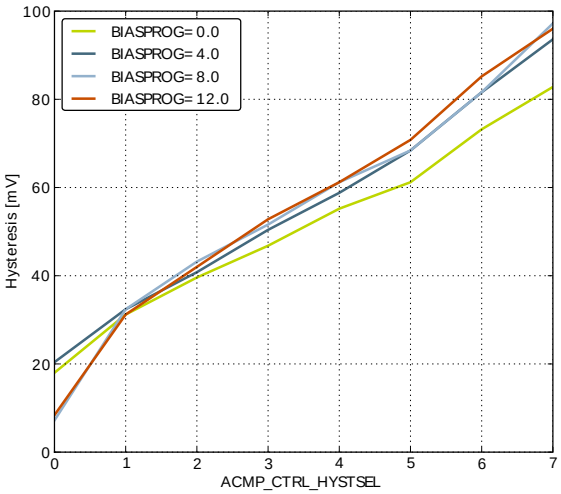
Figure 3.37. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



Current consumption, HYSTSEL = 4



Response time



Hysteresis

3.16 USART SPI

Figure 3.38. SPI Master Timing

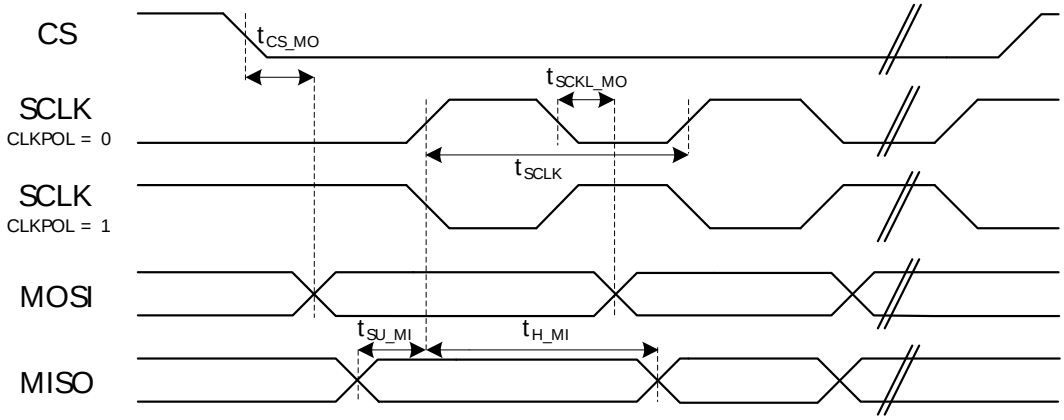


Table 3.23. SPI Master Timing

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{SCLK} [1] [2]	SCLK period		2 * $t_{HFPER-CLK}$			ns
t_{CS_MO} [1] [2]	CS to MOSI		-2.00		2.00	ns
t_{SCLK_MO} [1] [2]	SCLK to MOSI		-1.00		3.00	ns
t_{SU_MI} [1] [2]	MISO setup time	IOVDD = 3.0 V	36.00			ns
t_{H_MI} [1] [2]	MISO hold time		-6.00			ns

[1]Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)
[2]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.24. SPI Master Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{SCLK} [1] [2]	SCLK period		2 * $t_{HFPER-CLK}$			ns
t_{CS_MO} [12]	CS to MOSI		-2.00		2.00	ns
t_{SCLK_MO} [12]	SCLK to MOSI		-1.00		3.00	ns
t_{SU_MI} [12]	MISO setup time	IOVDD = 3.0 V	-32.00			ns
t_{H_MI} [12]	MISO hold time		63.00			ns

[1]Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)
[2]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

Symbol	Parameter	Min	Typ	Max	Unit
t_{SCLK_MI} [1][2]	SCLK to MISO	-264 + $t_{HF-PERCLK}$		-234 + 2 * $t_{HFPERCLK}$	ns

[1]Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)
[2]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

3.17 Digital Peripherals

Table 3.27. Digital Peripherals

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{USART}	USART current	USART idle current, clock enabled		4.0		µA/MHz
I_{UART}	UART current	UART idle current, clock enabled		3.8		µA/MHz
I_{LEUART}	LEUART current	LEUART idle current, clock enabled		194.0		nA
I_{I2C}	I2C current	I2C idle current, clock enabled		7.6		µA/MHz
I_{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		6.5		µA/MHz
$I_{LETIMER}$	LETIMER current	LETIMER idle current, clock enabled		85.8		nA
I_{PCNT}	PCNT current	PCNT idle current, clock enabled		91.4		nA
I_{RTC}	RTC current	RTC idle current, clock enabled		54.6		nA
I_{AES}	AES current	AES idle current, clock enabled		1.8		µA/MHz
I_{GPIO}	GPIO current	GPIO idle current, clock enabled		3.4		µA/MHz
I_{PRS}	PRS current	PRS idle current		3.9		µA/MHz
I_{DMA}	DMA current	Clock enable		10.9		µA/MHz

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32WG230.

4.1 Pinout

The *EFM32WG230* pinout is shown in Figure 4.1 (p. 53) and Table 4.1 (p. 53). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32WG230 Pinout (top view, not to scale)

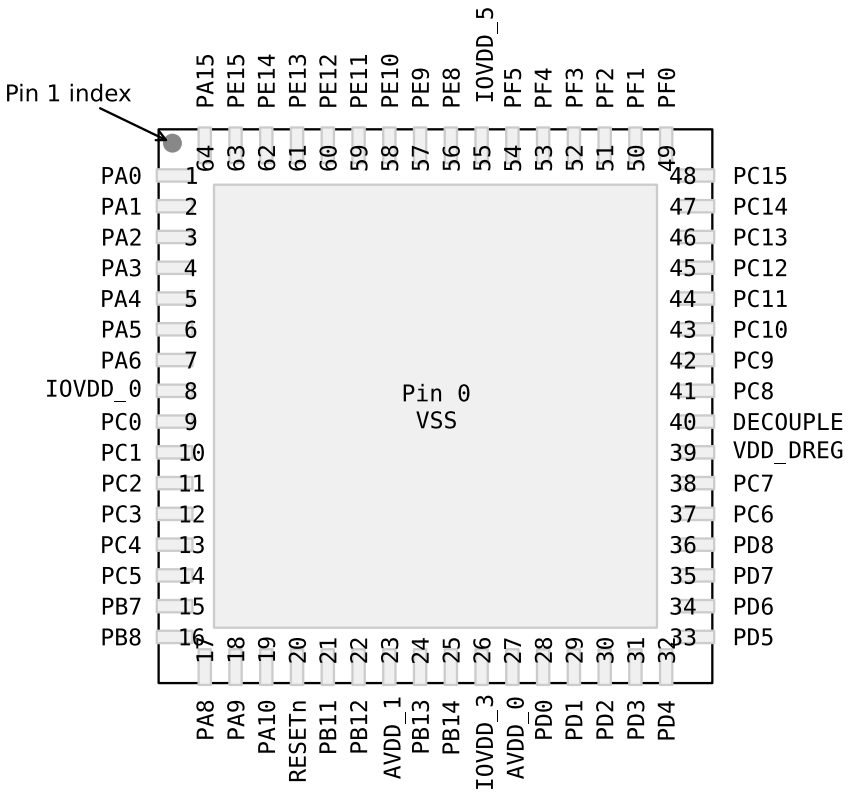


Table 4.1. Device Pinout

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
0	VSS	Ground			
1	PA0		TIM0_CC0 #0/1/4	LEU0_RX #4 I2C0_SDA #0	PRS_CH0 #0 GPIO_EM4WU0
2	PA1		TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
		OPAMP_OUT2 #1			
29	PD1	ADC0_CH1 DAC0_OUT1ALT #4/ OPAMP_OUT1ALT	TIM0_CC0 #3 PCNT2_S1IN #0	US1_RX #1	DBG_SWO #2
30	PD2	ADC0_CH2	TIM0_CC1 #3	US1_CLK #1	DBG_SWO #3
31	PD3	ADC0_CH3 OPAMP_N2	TIM0_CC2 #3	US1_CS #1	ETM_TD1 #0/2
32	PD4	ADC0_CH4 OPAMP_P2		LEU0_TX #0	ETM_TD2 #0/2
33	PD5	ADC0_CH5 OPAMP_OUT2 #0		LEU0_RX #0	ETM_TD3 #0/2
34	PD6	ADC0_CH6 DAC0_P1 / OPAMP_P1	TIM1_CC0 #4 LETIM0_OUT0 #0 PCNT0_S0IN #3	US1_RX #2 I2C0_SDA #1	LES_ALTEX0 #0 ACMP0_O #2 ETM_TD0 #0
35	PD7	ADC0_CH7 DAC0_N1 / OPAMP_N1	TIM1_CC1 #4 LETIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2 ETM_TCLK #0
36	PD8	BU_VIN			CMU_CLK1 #1
37	PC6	ACMP0_CH6		LEU1_TX #0 I2C0_SDA #2	LES_CH6 #0 ETM_TCLK #2
38	PC7	ACMP0_CH7		LEU1_RX #0 I2C0_SCL #2	LES_CH7 #0 ETM_TD0 #2
39	VDD_DREG	Power supply for on-chip voltage regulator.			
40	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size $C_{DECOUPLE}$ is required at this pin.			
41	PC8	ACMP1_CH0	TIM2_CC0 #2	US0_CS #2	LES_CH8 #0
42	PC9	ACMP1_CH1	TIM2_CC1 #2	US0_CLK #2	LES_CH9 #0 GPIO_EM4WU2
43	PC10	ACMP1_CH2	TIM2_CC2 #2	US0_RX #2	LES_CH10 #0
44	PC11	ACMP1_CH3		US0_TX #2	LES_CH11 #0
45	PC12	ACMP1_CH4 DAC0_OUT1ALT #0/ OPAMP_OUT1ALT			CMU_CLK0 #1 LES_CH12 #0
46	PC13	ACMP1_CH5 DAC0_OUT1ALT #1/ OPAMP_OUT1ALT	TIM0_CDTI0 #1/3 TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0		LES_CH13 #0
47	PC14	ACMP1_CH6 DAC0_OUT1ALT #2/ OPAMP_OUT1ALT	TIM0_CDTI1 #1/3 TIM1_CC1 #0 PCNT0_S1IN #0	US0_CS #3	LES_CH14 #0
48	PC15	ACMP1_CH7 DAC0_OUT1ALT #3/ OPAMP_OUT1ALT	TIM0_CDTI2 #1/3 TIM1_CC2 #0	US0_CLK #3	LES_CH15 #0 DBG_SWO #1
49	PF0		TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 LEU0_TX #3 I2C0_SDA #5	DBG_SWCLK #0/1/2/3
50	PF1		TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 LEU0_RX #3 I2C0_SCL #5	DBG_SWDIO #0/1/2/3 GPIO_EM4WU3
51	PF2		TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
52	PF3		TIM0_CDTI0 #2/5		PRS_CH0 #1 ETM_TD3 #1

3. Dimension 'b' applies to metallized terminal and is measured between 0.25 mm and 0.30 mm from the terminal tip. Dimension L1 represents terminal full back from package edge up to 0.1 mm is acceptable.
4. Coplanarity applies to the exposed heat slug as well as the terminal.
5. Radius on terminal is optional

Table 4.4. QFN64 (Dimensions in mm)

Symbol	A	A1	A3	b	D	E	D2	E2	e	L	L1	aaa	bbb	ccc	ddd	eee
Min	0.80	0.00		0.20			7.10	7.10		0.40	0.00					
Nom	0.85	-	0.203 REF	0.25	9.00 BSC	9.00 BSC	7.20	7.20	0.50 BSC	0.45		0.10	0.10	0.10	0.05	0.08
Max	0.90	0.05		0.30			7.30	7.30		0.50	0.10					

The QFN64 Package uses Nickel-Palladium-Gold preplated leadframe.

All EFM32 packages are RoHS compliant and free of Bromine (Br) and Antimony (Sb).

For additional Quality and Environmental information, please see:
http://www.silabs.com/support/quality/pages/default.aspx

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WONDER
ARM Cortex-M4